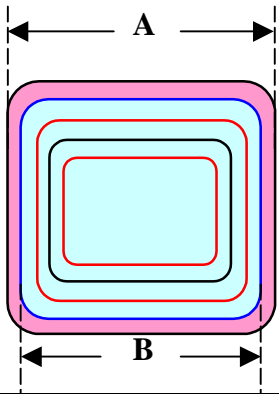


<b>Features :</b> <ul style="list-style-type: none"> <li>* Extremely low forward volts</li> <li>* Guard ring protection</li> <li>* Low reverse leakage current</li> </ul> 	Chip size(A):	0.889 * 0.889 mm <sup>2</sup>		
	Bond Pad size(B) :	0.762 * 0.762 mm <sup>2</sup>		
	Thickness :	300μm ± 20μm		
	Metalization :	Anode Ti/Ni/Ag		
	Metalization :	Cathode Ti/Ni/Ag		
<b>Electrical Characteristics</b>		Sym.	Spec. Limit	Unit
Maximum Instantaneous Forward Volt at IF : 1.0Amp. 25°C		VF max	0.83	Volt
Minimum Instantaneous Reverse Voltage at IR : 200 uA 25°C		VR min.	83	Volt.
Minimum Non-repetitive Peak Surge current at 25°C		IFSM	30	Amp
Storage Temperature		TSTG	-65 to +125	°C

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